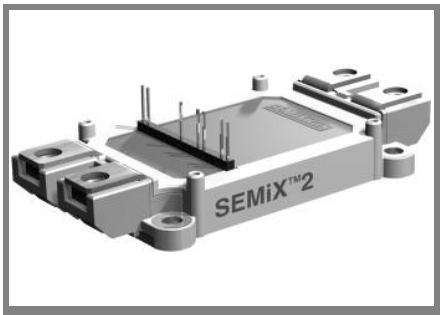
SEMiX 302GB128D



SEMiX® 2

SPT IGBT Modules

SEMiX 302GB128D

Preliminary Data

Features

- Homogeneous Si
- SPT = Soft-Punch-Through technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability

Typical Applications

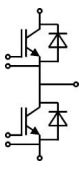
- AC inverter drives
- UPS
- Electronic welders up to 20 kHz

Remarks

- Not for new design

Absolute Maximum Ratings	T_{case} = 25°C, unless otherwise specified			
Symbol	**Conditions**		**Values**	**Units**
IGBT				
V_{CES}	T_j = 25 °C		1200	V
I_C	T_j = 150 °C	T_{case} = 25 °C	285	A
		T_{case} = 80 °C	200	A
I_{CRM}	I_{CRM}=2xI_{Cnom}		300	A
V_{GES}			±20	V
t_{psc}	V_{CC} = 600 V; $V_{GE} \leq$ 20 V; V_{CES} < 1200 V	T_j = 125 °C	10	µs
Inverse Diode				
I_F	T_j = 150 °C	T_{case} = 25 °C	230	A
		T_{case} = 80 °C	160	A
I_{FRM}	I_{FRM}=2xI_{Fnom}		300	A
I_{FSM}	t_p = 10 ms; sin.	T_j = 25 °C	1300	A
Module				
$I_{t(RMS)}$			600	A
T_{vj}			-40 ... + 150	°C
T_{stg}			-40 ... + 125	°C
V_{isol}	AC, 1 min.		4000	V

Characteristics	T_{case} = 25°C, unless otherwise specified					
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
IGBT						
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 6 mA		4,5	5	6,5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T_j = 25 °C			0,3	mA
V_{CE0}		T_j = 25 °C		1	1,15	V
		T_j = 125 °C		0,9	1,05	V
r_{CE}	V_{GE} = 15 V	T_j = 25°C		6	8	mΩ
		T_j = 125°C		8	10	mΩ
$V_{CE(sat)}$	I_{Cnom} = 150 A, V_{GE} = 15 V	T_j = 25°C$_{chiplev.}$		1,9	2,35	V
		T_j = 125°C$_{chiplev.}$		2,1	2,55	V
C_{ies}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		13,8		nF
C_{oes}				0,92		nF
C_{res}				0,58		nF
Q_G	V_{GE} = -8 V ... +15 V			1450		nC
$t_{d(on)}$	R_{Gon} = 4 Ω	V_{CC} = 600V		190		ns
t_r		I_{Cnom}= 150A		51		ns
E_{on}		T_j = 125 °C		17		mJ
$t_{d(off)}$	R_{Goff} = 4 Ω			466		ns
t_f				56		ns
E_{off}				16		mJ
$R_{th(j-c)}$	per IGBT				0,11	K/W



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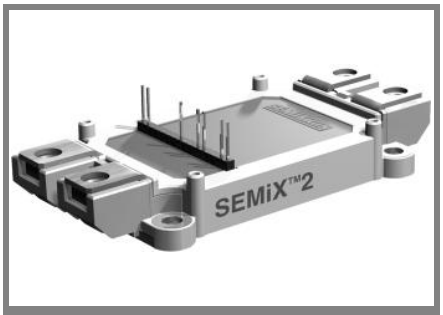

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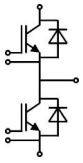

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Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
Inverse Diode						
$V_F = V_{EC}$	I_{Fnom} = 150 A; V_{GE} = 0 V	T_j = 25 °C$_{chiplev.}$		2	2,5	V
		T_j = 125 °C$_{chiplev.}$		1,8	2,3	V
V_{F0}		T_j = 25 °C		1,1	1,45	V
		T_j = 125 °C		0,85	1,2	V
r_F		T_j = 25 °C		6	7	mΩ
		T_j = 125 °C		6,3	7,3	mΩ
I_{RRM}	I_{Fnom} = 150 A	T_j = 125 °C		180		A
Q_{rr}	di/dt = 4300 A/µs			22		µC
E_{rr}	V_{GE} = -15 V; V_{CC} = 600 V			8		mJ
$R_{th(j-c)D}$	per diode				0,19	K/W
Module						
L_{CE}				18		nH
$R_{CC'+EE'}$	res., terminal-chip	T_{case}= 25 °C		0,7		mΩ
		T_{case}= 125 °C		1		mΩ
$R_{th(c-s)}$	per module			0,045		K/W
M_s	to heat sink (M5)		3		5	Nm
M_t	to terminals (M6)		2,5		5	Nm
w					250	g
Temperature sensor						
R_{100}	T_c=100°C (R_{25}=5 kΩ)			0,493±5%		kΩ
$B_{100/125}$	$R(T)=R_{100}\exp[B_{100/125}(1/T-1/T_{100})]$; T[K]; B			3550±2%		K

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

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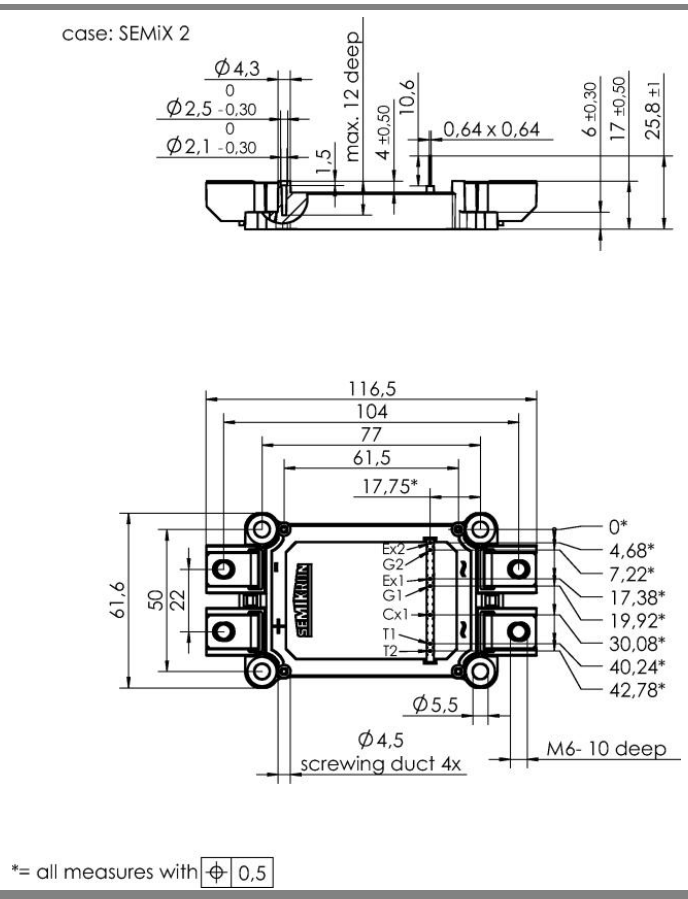
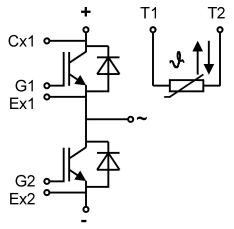


Case SEMiX 2



Pinout GB

